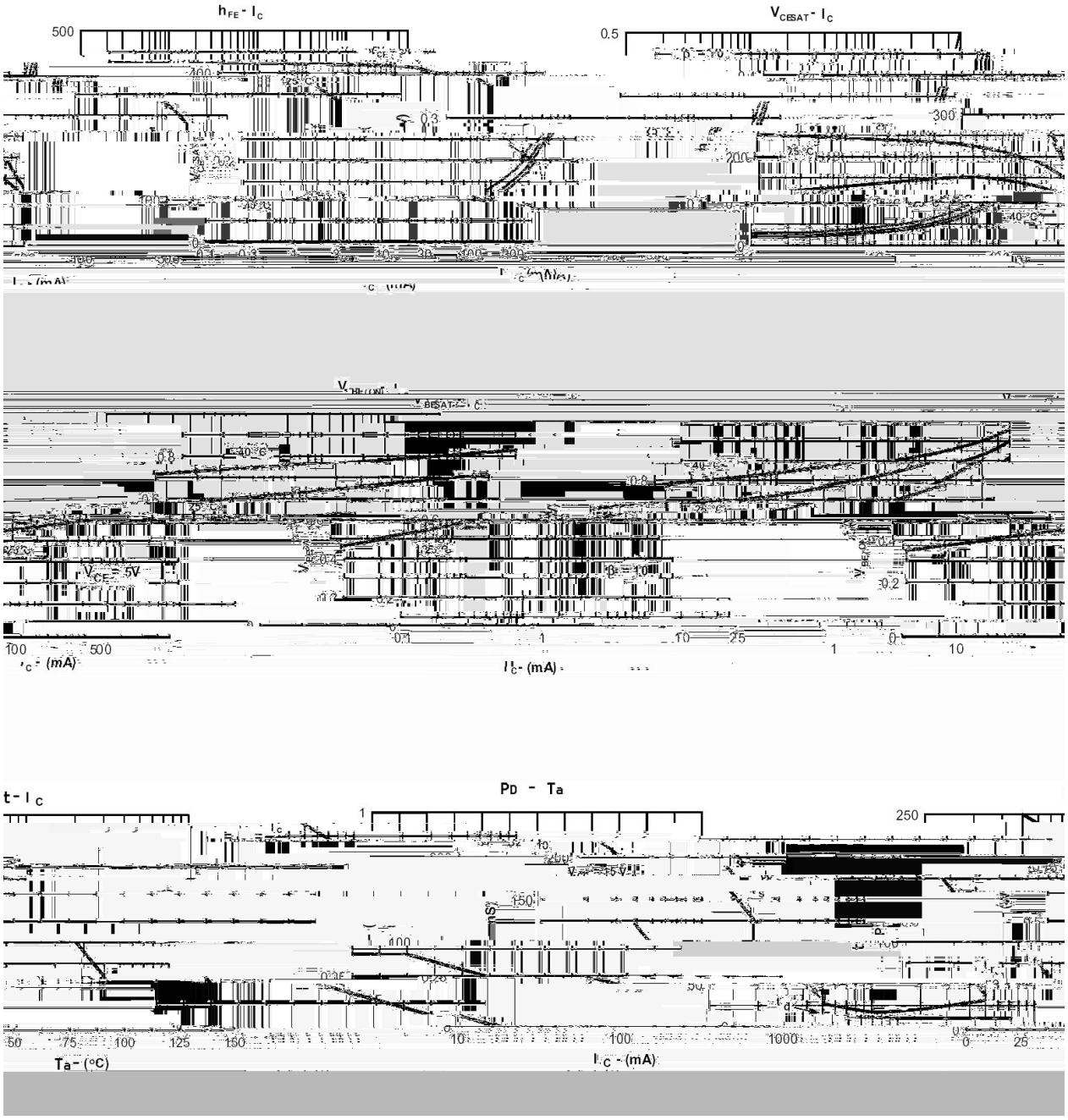
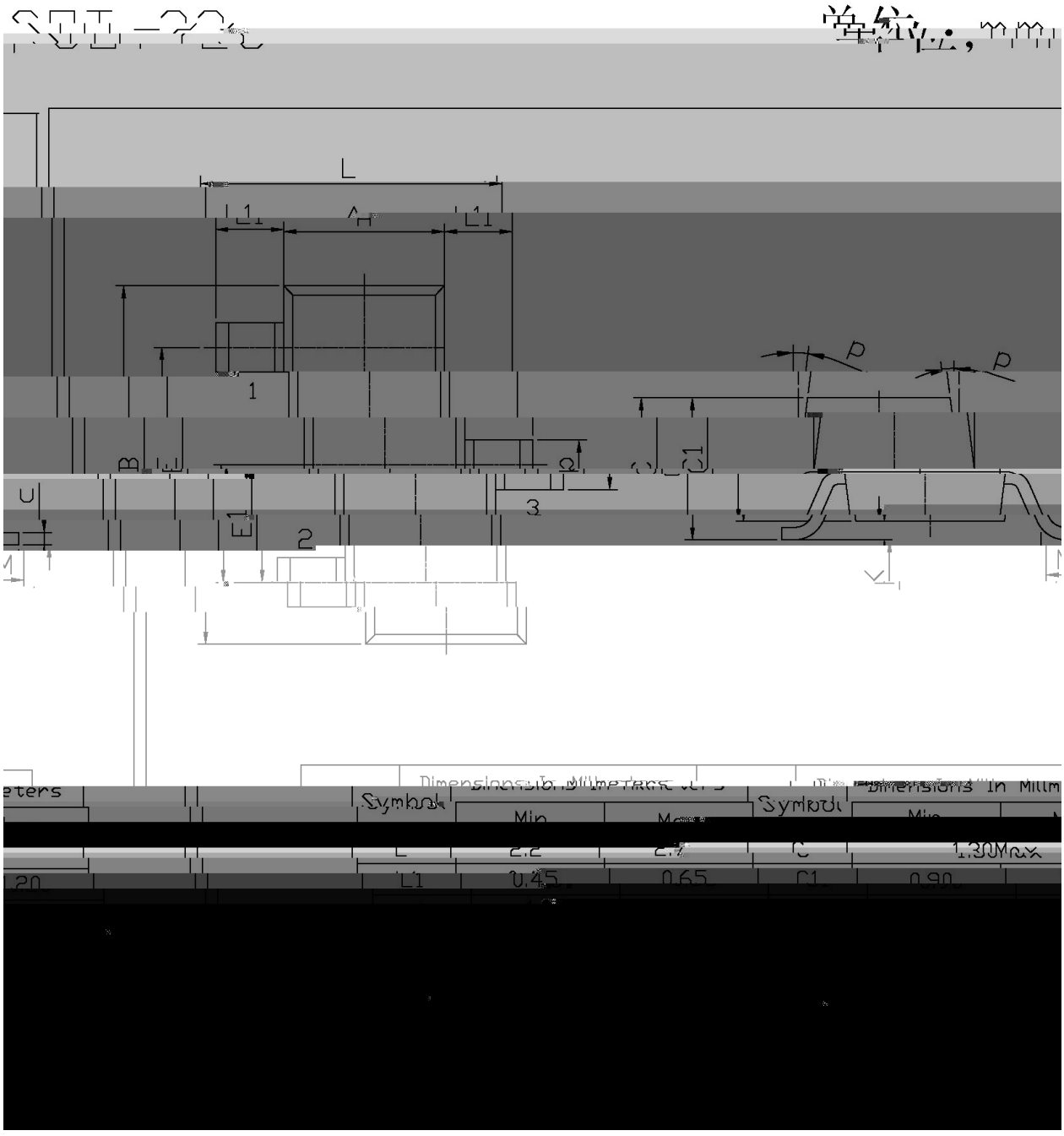
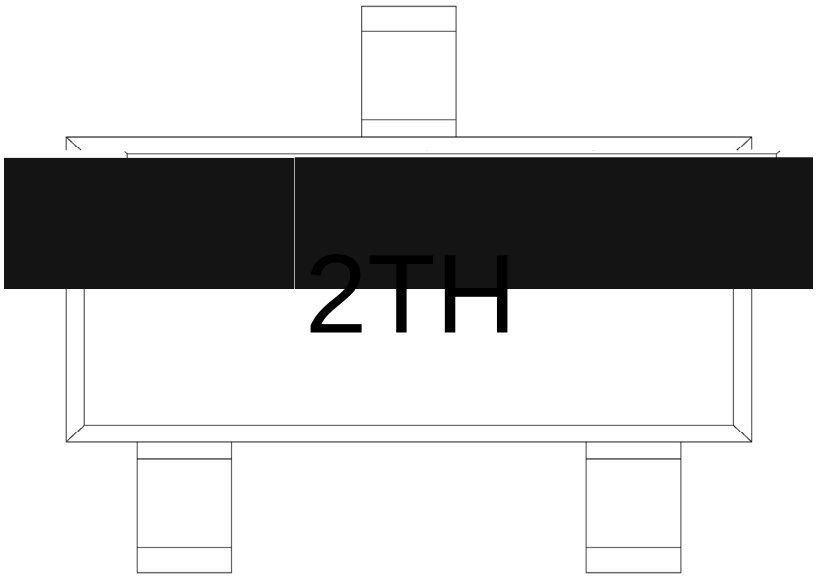
SOT-23 PNP

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-40V I_E=0			-50	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-50	nA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-150mA	100		300	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-0.1mA	30			
	$h_{FE(3)}$	V_{CE}=-1.0V I_C=-1.0mA	60			
	$h_{FE(4)}$	V_{CE}=-1.0V I_C=-10mA	100			
	$h_{FE(5)}$	V_{CE}=-2.0V I_C=-500mA	20			
Collector-Emitter Saturation voltage	$V_{CE(sat)\ (1)}$	I_C=-150mA I_B=-15mA			-0.4	V
	$V_{CE(sat)\ (2)}$	I_C=-500mA I_B=-50mA			-0.75	V
Base-Emitter Saturation Voltage	$V_{BE(sat)\ (1)}$	I_C=-150mA I_B=-15mA	-0.75		-0.95	V
	$V_{BE(sat)\ (2)}$	I_C=-500mA I_B=-50mA			-1.3	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-20mA f=100MHz	200			MHz
Delay Time	t_d	V_{CC}=-30V I_C=-150mA I_{B1}=-15mA			15	ns
Rise Time	t_r				20	ns
Storage Time	t_s	V_{CC}=-30V I_C=-150mA I_{B1}=I_{B2}=-15mA			225	ns
Fall Time	t_f				30	ns


h_{FE} - I_C
500
100
0.3
0
0.1
0.3
1
3
10
30
100
300
V_{CESAT} - I_C
0.5
300
200
40°C
I_C - (mA)
V_{CE} = 5V
0.8
0.4
0.2
0.1
1
10
25
1
0
10
100
500
I_C - (mA)
I_C - (mA)
t - I_C
P_D - Ta
1
10
250
150
100
50
75
100
125
150
10
100
1000
0
25
Ta - (°C)
I_C - (mA)


L
L1
H
L1
P
P
1
B
C
C1
3
D
E1
2
Symbol
Min
Symbol
L
2.2
C
1.30Max
L1
0.45
0.65
C1
0.90



2T

H

Note:

2T	Product Type Code
H	Company Code